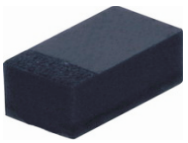
SMD Schottky Barrier Diode

COMCHIP
SMD Diodes Specialist

CDBER0140R(RoHs Device)

Io = 100 mA
V_R = 40 Volts



Features

- Low reverse current.
- Designed for mounting on small surface.
- Extremely thin/leadless package.
- Majority carrier conduction.

Mechanical data

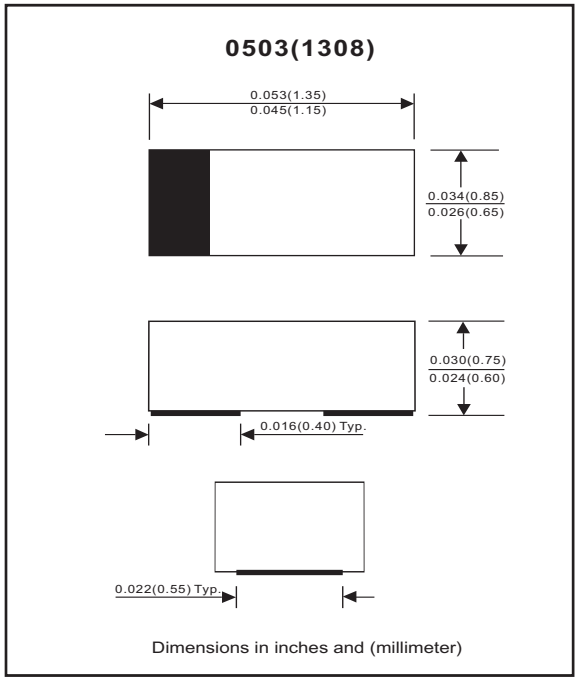
Case: 0503(1308) standard package, molded plastic.

Terminals: Gold plated, solderable per MIL-STD-750,method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.002 gram(approx.).



Maximum Rating (at T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive Peak reverse voltage		V_{RRM}			45	V
Reverse voltage		V_R			40	V
Average forward rectified current		I_O			100	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load (JEDEC method)	I_{FSM}			1	A
Storage temperature		T_{STG}	-40		+125	°C
Junction temperature		T_j			+125	°C

Electrical Characteristics (at T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 10mA	V_F			0.45	V
Reverse current	V_R = 10V	I_R			1	uA
Capacitance between terminals	f = 1 MHz, and 10 VDC reverse voltage	C_T		6		pF

RATING AND CHARACTERISTIC CURVES (CDBER0140R)

Fig. 1 - Forward characteristics

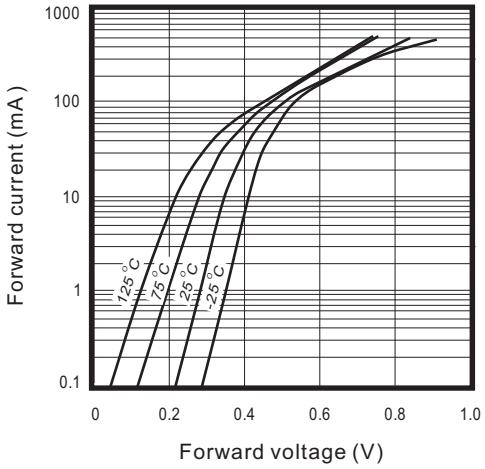


Fig. 2 - Reverse characteristics

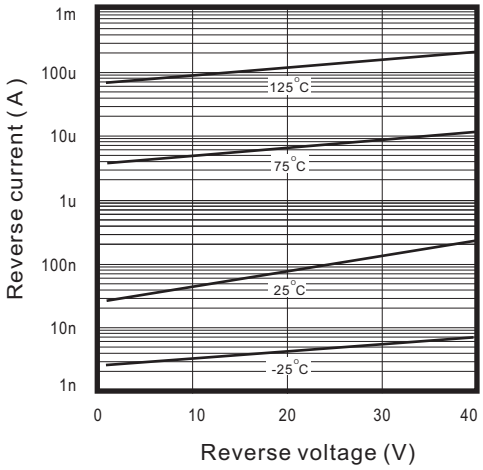


Fig. 3 - Capacitance between terminals characteristics

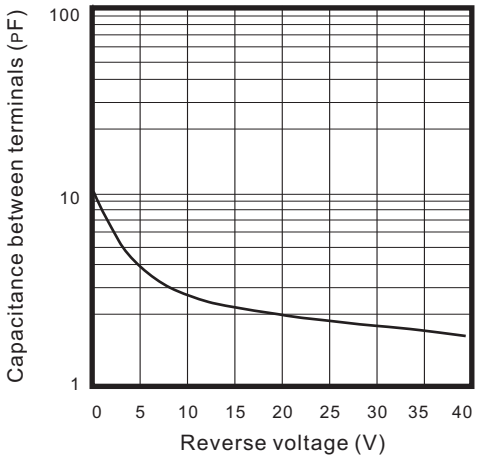


Fig.4 - Current derating curve